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TITLE : COMPOSITION FOR FORMING FILM, FORMATION OF FILM AND LOW- DENSITY FILM

ABSTRACT : PROBLEM TO BE SOLVED: To obtain a composition for forming a film having excellent dielectric constant characteristics, mechanical strength, etc.

SOLUTION: This composition for forming a film comprises (A) a silane compound which is a hydrolyzate and a condensate or either of the hydrolyzate and the condensate of at least one compound selected from the group consisting of a compound of the formula, R1aSi(OR2)4-a (R1 is a hydrogen atom, a fluorine atom or a monofunctional organic group; R2 is a monofunctional organic group; and (a) is an integer of 0-2) and a compound of the formula, R3b(R4O)3-bSi-(R7)d- Si(OR5)3-cR6c (R3, R4, R5 and R6 are each the same or different and a monofunctional organic group; (b) and (c) are each the same or different and an integer of 0-2; R7 is an oxygen atom or a group of -(CH2)n; (n) is 1-6; and (d) is 0 or 1), (B) a latent basic catalyst and (C) a compound which is compatible or dispersible in the component A and has 250-450°C decomposition temperature.

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